

P-Channel Enhancement Mode Power MOSFET

Description

The RM70P30LD uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications. It is ESD protected.

General Features

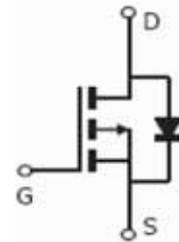
- $V_{DS} = -30V, I_D = -70A$
 $R_{DS(ON)} < 7.2m\Omega @ V_{GS} = -10V$
 $R_{DS(ON)} < 12m\Omega @ V_{GS} = -4.5V$
- Super high dense cell design
- Advanced trench process technology
- Reliable and rugged
- High density cell design for ultra low on-resistance

Application

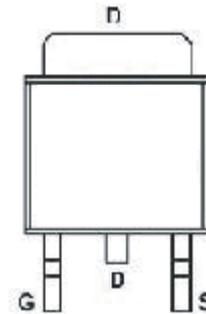
- Power switch
- DC/DC converters
- Halogen-free
- P/N suffix V means AEC-Q101 qualified, e.g: RM70P30LDV

100% UIS TESTED!

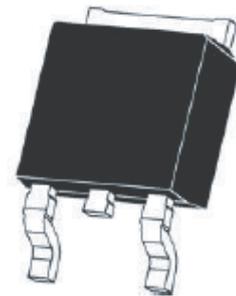
100% ΔV_{ds} TESTED!



Schematic diagram



Marking and pin assignment



TO-252 -2L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
70P30	RM70P30LD	TO-252-2L	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-70	A
Drain Current-Continuous ($T_C = 100^\circ C$)	$I_D(100^\circ C)$	-50	A
Pulsed Drain Current	I_{DM}	-200	A
Maximum Power Dissipation	P_D	90	W
Single pulse avalanche energy ^(Note 5)	E_{AS}	80	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	$R_{\theta jc}$	1.6	$^{\circ}\text{C}/\text{W}$
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Electrical Characteristics ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-24V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.2	-	-2.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-20A$	-	6	7.2	m Ω
		$V_{GS}=-4.5V, I_D=-15A$	-	9.5	12	
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	$V_{DS}=-25V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	3450	-	PF
Output Capacitance	C_{oss}		-	255	-	PF
Reverse Transfer Capacitance	C_{rss}		-	140	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-15V, I_D=-10A$ $V_{GS}=-20V, R_{GEN}=3.3\Omega$	-	17	-	nS
Turn-on Rise Time	t_r		-	40	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	55	-	nS
Turn-Off Fall Time	t_f		-	13	-	nS
Total Gate Charge	Q_g	$V_{DS}=-15V, I_D=-18A,$ $V_{GS}=-10V$	-	60	-	nC
Gate-Source Charge	Q_{gs}		-	9	-	nC
Gate-Drain Charge	Q_{gd}		-	15	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=-1A$	-	-	-1.2	V
Diode Forward Current (Note 2)	I_S	-	-	-	-70	A
Reverse Recovery Time	t_{rr}	$T_J=25^{\circ}\text{C}, I_F=-20A$ $di/dt=100A/\mu s$ (Note 3)	-	22	-	nS
Reverse Recovery Charge	Q_{rr}		-	72	-	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. E_{AS} condition: $T_J=25^{\circ}\text{C}, V_{DD}=-50V, V_G=-10V, L=0.5\text{mH}, R_g=25\Omega$

RATING AND CHARACTERISTICS CURVES (RM70P30LD)

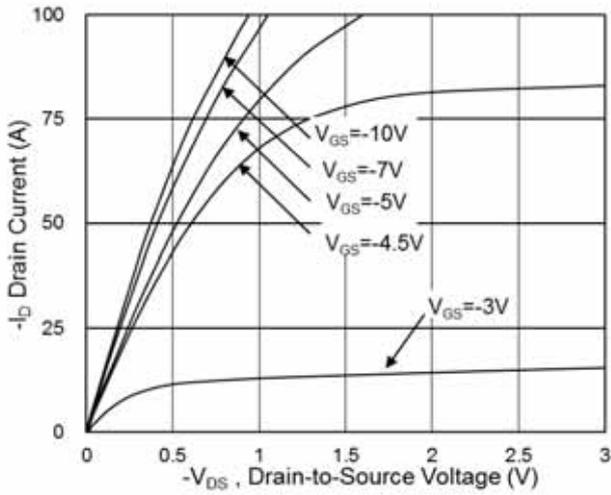


Fig.1 Typical Output Characteristics

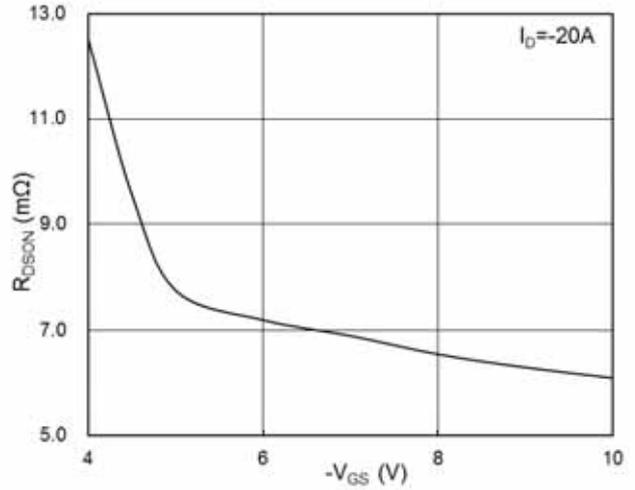


Fig.2 On-Resistance vs. Gate-Source Voltage

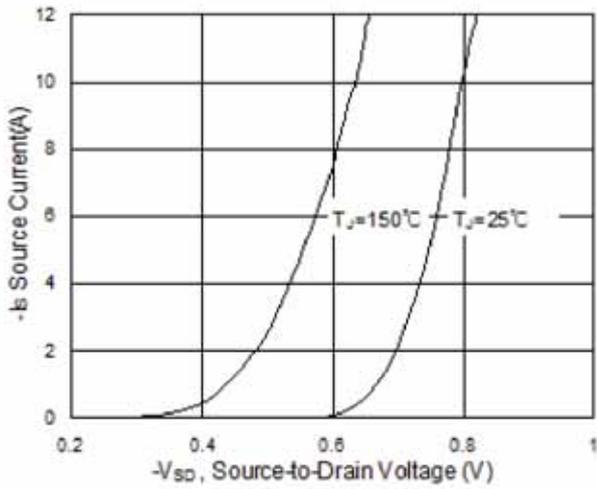


Fig.3 Forward Characteristics of Reverse

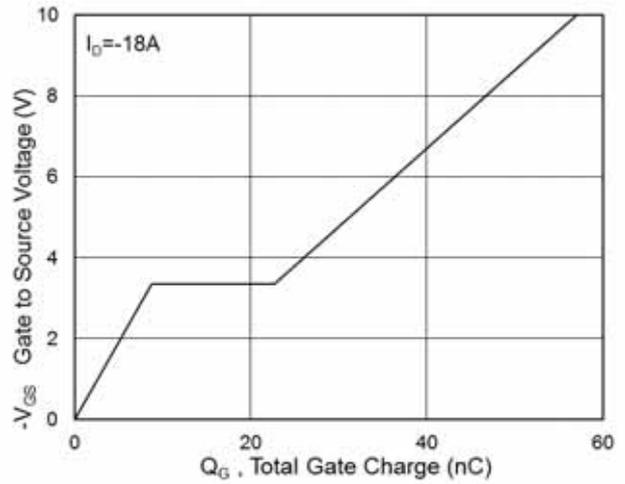


Fig.4 Gate-Charge Characteristics

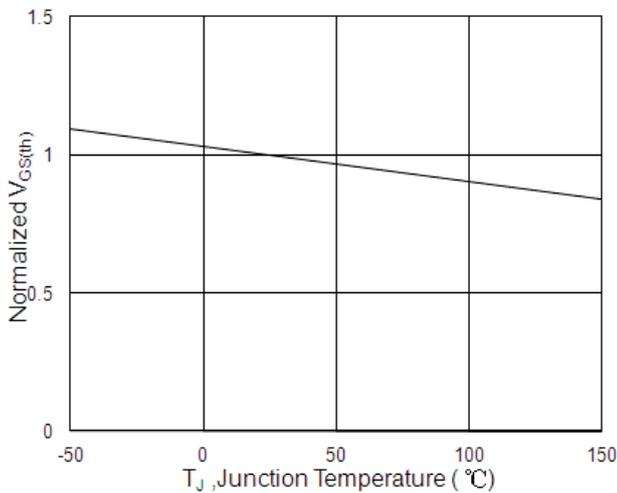


Fig.5 Normalized $-V_{GS(th)}$ vs. T_J

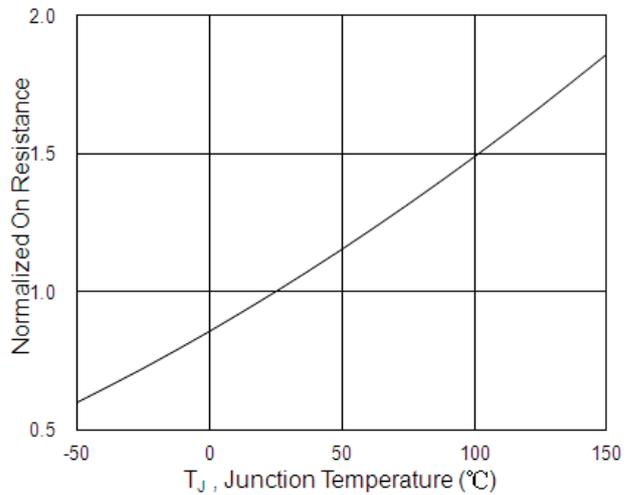


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

RATING AND CHARACTERISTICS CURVES (RM70P30LD)

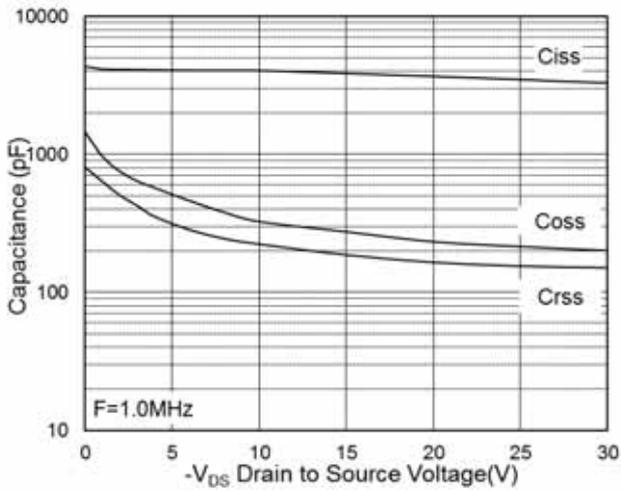


Fig.7 Capacitance

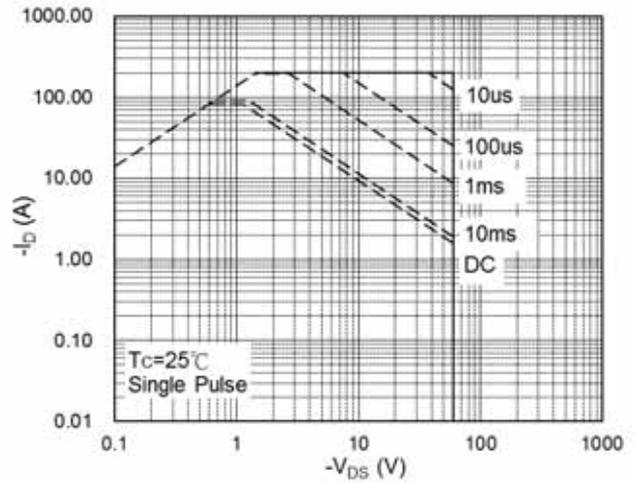


Fig.8 Safe Operating Area

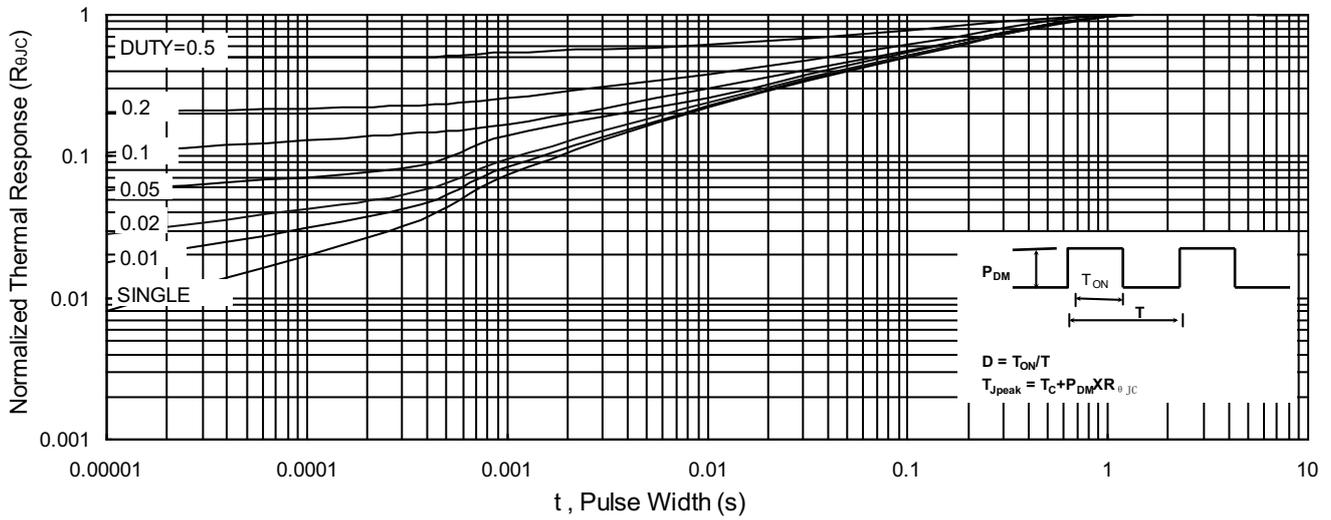


Fig.9 Normalized Maximum Transient Thermal Impedance

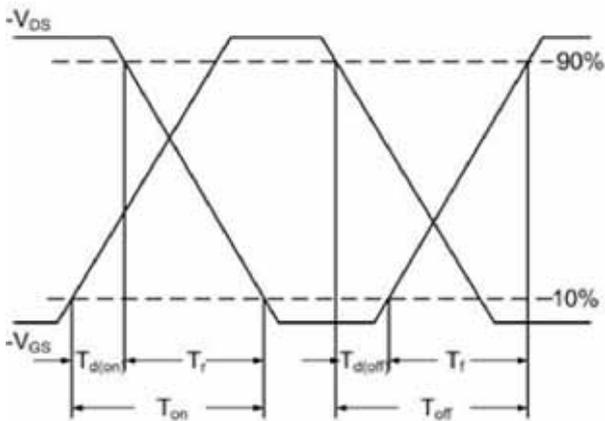


Fig.10 Switching Time Waveform

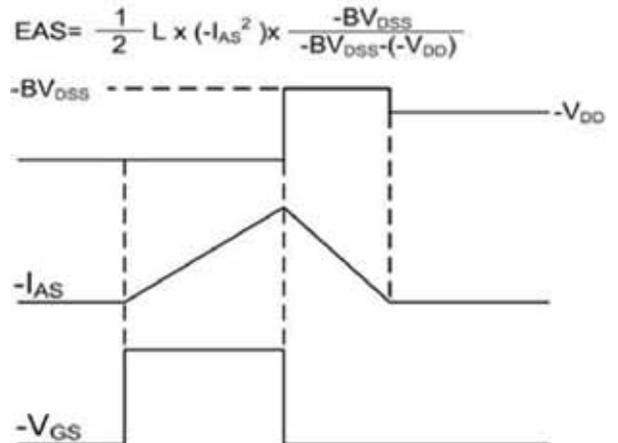
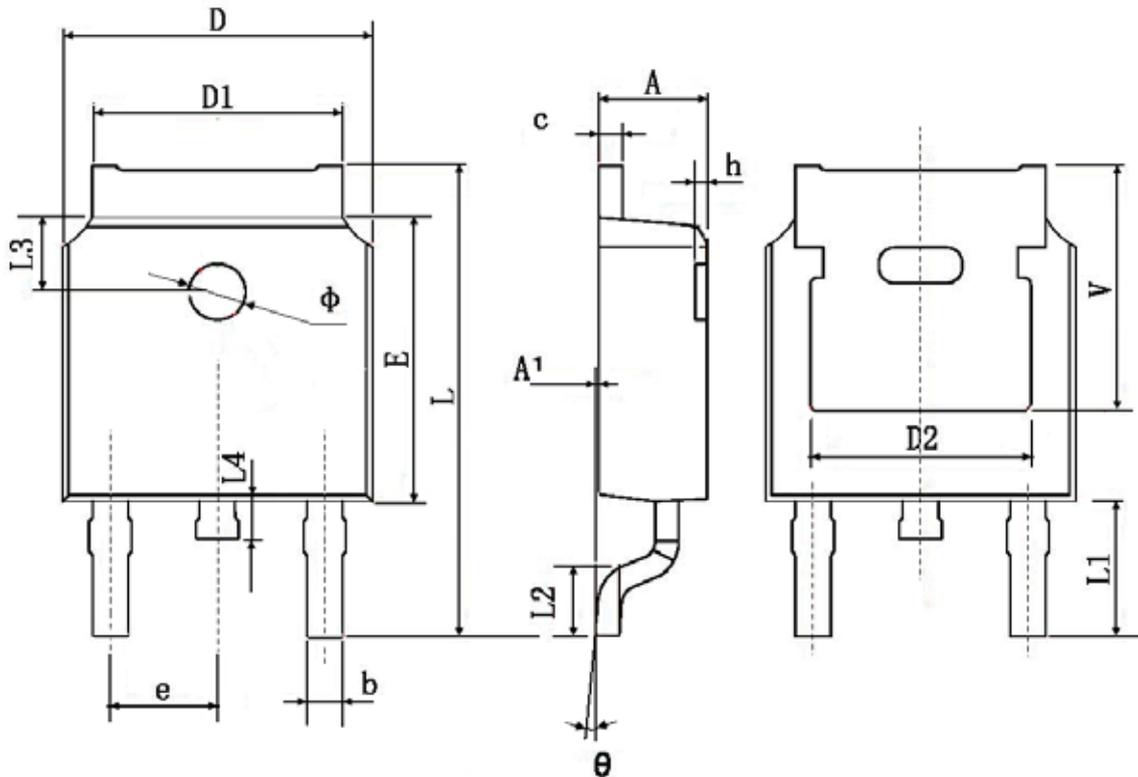


Fig.11 Unclamped Inductive Switching Waveform

TO-252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
phi	1.100	1.300	0.043	0.051
theta	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	

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